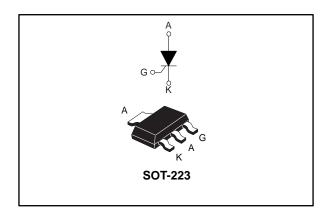
P0111MN



Sensitive 0.8 A SCR thyristor

Datasheet - production data



Features

- I_{T(RMS)} 0.8 A
- 125 °C max T_i
- Low 0.004 to 0.025 mA gate current
- 600 V V_{DRM}/V_{RRM}
- ECOPACK®2 compliant component

Applications

- Proximity sensors
- Gate driver for large thyristors
- Overvoltage crowbar protection
- Ground fault circuit interrupters
- Arc fault circuit interrupter
- Solid state relay pilot circuit
- Standby mode power supplies
- Residual current detector

Description

Thanks to highly sensitive triggering levels, the 0.8 A P0111MN SCR thyristor is suitable for all applications where available gate current is limited. This device offers a high blocking voltage of 600 V, ideal for applications like interrupters circuits.

The surface mount SOT-223 package allows compact, SMD based designs for automated manufacturing.

Table 1: Device summary

Symbol	Value	Unit		
I _{T(RMS)}	0.8	Α		
V _{DRM} /V _{RRM}	600	V		
l _{GT}	0.004 to 0.025	mA		
T _j max.	125	°C		

Characteristics P0111MN

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), T_j = 25 °C unless otherwise specified

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (180 ° cond		0.8		
I _{T(AV)}	Average on-state current (180 ° conduction angle)		T _{amb} = 70 °C	0.5	А
I	Non repetitive surge peak on-state	e current	$t_p = 8.3 \text{ ms}$	8	Α
Ітѕм	$(T_j \text{ initial} = 25 °C)$		$t_p = 10 \text{ ms}$	7	A
l ² t	I ² t value for fusing	$t_p = 10 \text{ ms}$	0.24	A ² s	
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	f = 60 Hz	T _j = 125 °C	50	A/µs
V _{DRM} /V _{RRM}	Repetitive peak off-state voltage	T _j = 125 °C	600	V	
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125 °C	1	Α
P _{G(AV)}	Average gate power dissipation	T _j = 125 °C	0.1	W	
T _{stg}	Storage junction temperature range		-40 to +150	°C	
Tj	Operating junction temperature		-40 to +125	°C	

Table 3: Electrical characteristics ($T_j = 25$ °C unless otherwise specified)

Symbol	Test conditions		Value	Unit	
I _{GT}	V 40 V B 440 O		Min Max.	0.004 to 0.025	mA
V _G T	$V_D = 12 \text{ V}, R_L = 140 \Omega$		Max.	0.8	V
V_{GD}	$V_D = V_{DRM},~R_L = 3.3~k\Omega,~R_{GK} = 1000~\Omega$	Min.	0.1	V	
V_{RG}	$I_{RG} = 10 \mu A$	Min.	8	V	
Ін	I_T = 50 mA, R_{GK} = 1000 Ω	Max.	5	mA	
IL	I_G = 1.2 x I_{GT} , R_{GK} = 1000 Ω		Max.	6	mA
dV/dt	$V_D = 67 \% V_{DRM}, R_{GK} = 1000 \Omega$ $T_j = 125 °C$		Min.	80	V/µs

Table 4: Static characteristics

Symbol	Test conditions			Value	Unit
V _{TM}	$I_{TM} = 1.6 \text{ A}, t_p = 380 \ \mu s$ $T_j = 25 \ ^{\circ}\text{C}$		Max.	1.95	V
Vто	Threshold voltage	T _j = 125 °C	Max.	0.95	V
R₀	Dynamic resistance	T _j = 125 °C	Max.	600	mΩ
1 /1	$V_D = V_{DRM}, V_R = V_{RRM},$ $R_{GK} = 1000 \Omega$		Mex	10	
IDRM/IRRM			Max.	100	μA

Table 5: Thermal parameters

Symbol	Paramete	Value	Unit	
$R_{th(j-t)}$	Junction to tab (DC)		30	
R _{th(j-a)}	Junction to ambient (DC)	$S^{(1)} = 5 \text{ cm}^2$	60	°C/W

Notes: (1)S = copper surface under tab.



P0111MN Characteristics

1.1 Characteristics (curves)

Figure 1: Maximum average power dissipation versus average on-state current

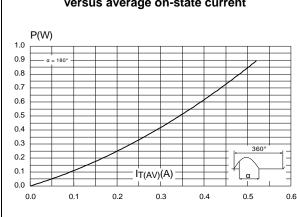


Figure 2: Average and DC on-state current versus case temperature $I_{T(AV)}(A)$ 1.0 0.9 0.8 0.7 0.6 $\alpha = 180^{\circ} (SOT-223)$ 0.5 0.4 0.3 0.2 0.1 T_{lead} (°C) 0.0 25 50 125 ٥ 100

Figure 3: Average and DC on-state current versus ambient temperature

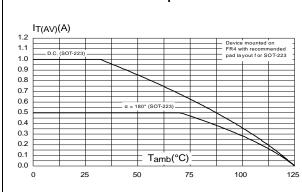


Figure 4: Relative variation of thermal impedance versus pulse duration

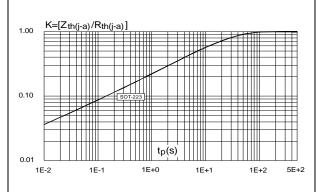


Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

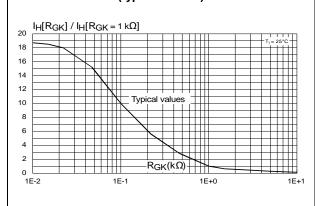
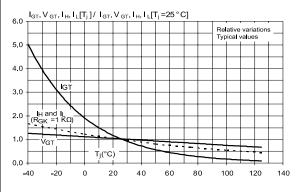


Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)



Characteristics P0111MN

immunity versus gate-cathode resistance (typical values)

dV/dt[R_{GK}] / dV/dt[R_{GK} = 1kΩ]

1.0

Typical values

R_{GK}(kΩ)

0.1

0.2

0.4

0.6

0.8

1.0

1.2

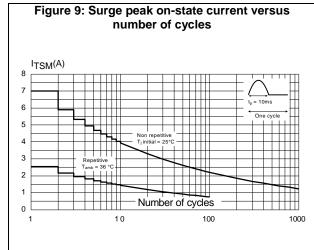
1.4

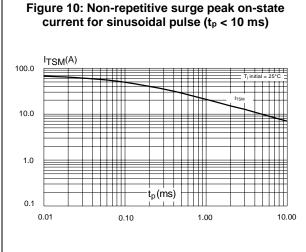
1.6

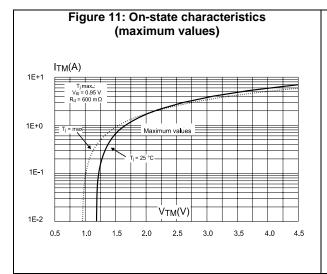
1.8

2.0

Figure 7: Relative variation of static dV/dt







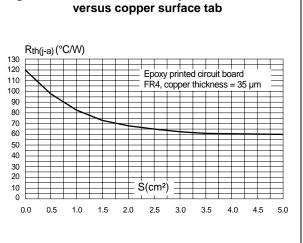


Figure 12: Thermal resistance junction to ambient

P0111MN Package information

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Lead-free package
- Halogen free molding resin
- Epoxy meets UL94, V0

2.1 SOT-223 package information

Figure 13: SOT-223 package outline

D
B1
1 2 3 0046067_14

Table 6: SOT-223 package mechanical data

Dim.	Millimeters				Inches ⁽¹⁾		
Dilli.	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.8			0.0709	
A1	0.02		0.1	0.0008		0.0039	
В	0.6	0.7	0.85	0.0236	0.0276	0.0335	
B1	2.9	3	3.15	0.1142	0.1181	0.1240	
С	0.24	0.26	0.35	0.0094	0.0102	0.0138	
D ⁽²⁾	6.3	6.5	6.7	0.2480	0.2559	0.2638	
е		2.3			0.0906		
e1		4.6			0.1811		
E	3.3	3.5	3.7	0.1299	0.1378	0.1457	
Н	6.7	7.0	7.3	0.2638	0.2756	0.2874	
V			10°			10°	

Notes:

3.3 6.4 (3x)1.5 4.6 0046067

Figure 14: SOT-223 recommended footprint (dimensions are in mm)

⁽¹⁾Inches dimensions given only for reference

 $^{^{(2)}}$ Does not include mold flash or protusions. Mold flash or protusions must not exceed 0.15 mm (0.006 inches)

P0111MN Ordering information

3 Ordering information

Figure 15: Ordering information scheme

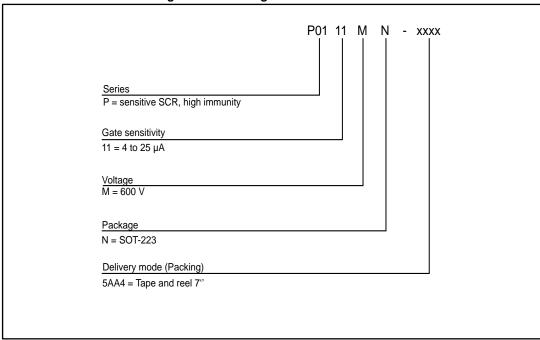


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
P0111MN 5AA4	P1M	SOT-223	0.12 g	1000	Tape and reel 7"

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
09-Oct-2017	1	Initial release.

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